

TABLE OF CONTENTS

BONDING TECHNOLOGY

Wafer Bonding and Layer Transfer for Microsystems: An Overview Qin-Yi Tong (invited)	1
SOI Materials and Device Development at IBM Fari Assaderaghi, Ghavam Shahidi (invited)	17
Formation of Silicon Structures by Plasma Activated Wafer Bonding P. Amirfeiz, S. Bengtsson, M. Bergh, E. Zanghellini, L. Börjesson	29
Strain and Strain Relaxation in SOI Materials J. Camassel, Planes, N. Falkovski, L., Moller, H. Eickhoff, M., Krötz, G.	40

EXFOLIATION TECHNOLOGIES

The Smart-Cut Process: Status and Developments B. Aspar, C. Lagahe, H. Moriceau, E. Jalaguier, A. Mas, O. Rayssac, Soubie, B. Biasse, M. Bruel, A. J. Auberton-Hevre, T. Barge, F. Letertre, C. Maleville (invited)	48
Wafer Bonding of Compound Semiconductors using Atomic Hydrogen T. Akatsu, A. Plössl, H. Stenzel, U. Gösele	60
Critical Bonding Energy Required for Hydrogen-Implantation Induced Layer Splitting L.-J. Huang, Q.-Y. Tong, U. M. Gösele	68

BONDING OF DISSIMILAR MATERIALS

Low Temperature Si-Si and GaAs-Si Direct Wafer Bonding using Spin-On Glass Intermediate Layer V. Dragoi, M. Alexe, M. Reiche	80
Relaxation Mechanisms of Strained SiGe Films Bonded to High and Low Viscosity Oxides K. D. Hobart, F. J. Kub, M. Fatemi, M. E. Twigg, P. E. Thompson, T. S. Kuan, C. K. Inoki	85
Hetero-Epitaxial Growth of 3C-SiC on SOI using HMDS P. Aboughe-Nze, N. Planes, M. Ravetz, B. Fraisse, S. Contreras, P. Vicente, T. Chassagne, Y. Monteil, S. Rushworth, J. Camassel	92

Bonding Behavior of Different Interfacial Layers M. Reiche, M. Wiegand, D. Stolze, U. Schwarz	100
--	-----

BONDING MECHANICS AND CHARACTERIZATION

Mesa-Spacers: Enabling Non-Destructive Measurements of Surface Energy in Room Temperature Wafer Bonding Donato Pasquariello, Klas Hjort	110
--	-----

Why Debonding is Useful in SOI G. Cha, S. H. Lee, H. J. Park, K. H. Lee, H. S. Kang, C. S. Song, D. J. Kim, Y. C. Kim, S. K. Kim	119
--	-----

Lifetime Properties of Wafer-Bonded Components under Static and Cyclic Loading J. Bagdahn, M. Petzold	129
--	-----

Oxidation Effect on Microcontamination and Bondability of Ultrathin Silicon Wafers M. Beggans, T. G. Digges, Jr., K. R. Farmer	137
---	-----

Factors Affecting Void Formation in Dielectric Isolation Wafers made by Bonding Hiroyuki Oi, Keiichi Tanaka, Etsuro Morita (invited)	146
---	-----

Failure Analysis and Investigation of Bondpad Peeling Problem during Bonding Y. N. Hua, S. P. Zhao, L. H. An, Z. R. Guo, Shailesh Redkar	161
---	-----

Oxidation and Induced Damages in Oxygen Plasma <i>In-Situ</i> Wafer Bonding Donato Pasquariello, Christer Hedlund, Klas Hjort	169
--	-----

Oxidation Induced Crystalline Defects in Bonded SOI Wafers P. Papakonstantinou, K. Somasundram, X. Cao, C. Quinn, K. Yallup, W. A. Nevin, S. Blackstone	178
---	-----

Photoluminescence Study of Interface Defects in Bonded Silicon Wafers W. A. Nevin, D. L. Gay, S. Blackstone, V. Higgs	187
--	-----

Wafer Contamination Protection by Direct Wafer Bonding and Air Jet Debonding M. Alexe, U. Gösele	195
---	-----

Preparation of Bonded Wafer Pairs M. Reiche, K. H. Priewasser, E. Wittenzellner, P. Nauert, W. Nadrag	200
--	-----

Weibull Fracture Probability for Silicon Wafer Bond Evaluation J. Köhler, K. Jonsson, S. Greek, L. Stenmark, Y. Bäcklund	209
---	-----

Measurement of the Local Strength Distribution of Directly Bonded Silicon Wafers using the Micro-Chevron Test J. Bagdahn, A. Plössl, M. Wiemer, M. Petzold	218
--	-----

Bonding of Hydrogen-Terminated Silicon: Thermal Evolution of the Interfacial Properties A. Plössl, R. Scholz, H.-J. Schulze, S. Hopfe	224
---	-----

LOW-TEMPERATURE AND UHV BONDING

Room Temperature Covalent Bonding: Effect on Interfacial Properties A Plössl, R. Scholz, T. Akatsu (Invited)	232
---	-----

Surface Passivation for Low-Temperature UHV Wafer Bonding of GaAs Substrates P. J. Hesse, T. W. Haas, W. V. Lampert, K. G. Eyink, D. H. Tomich, M. L. Seaford	244
---	-----

Recent Developments In Adhesion-Enhanced High-Vacuum Bonding By <i>In Situ</i> Plasma Surface Precleaning P. Kopperschmidt, H.C. Luan, L.C. Kimerling	259
---	-----

Room-Temperature Wafer Bonding Using Ar Beam Surface Activation H. Takagi, R. Maeda, N. Hosoda, T.R. Chung, T. Suga	265
--	-----

Interface Chemistry of Tailor-Made Monolayers For Low-Temperature Wafer Bonding G. Kräuter, Y. Bluhm	275
---	-----

Effect of O ₂ Plasma Pretreatment on the Bonding Behavior of Silicon (100) Wafers M. Wiegand, G. Kräuter, M. Reiche	282
---	-----

Plasma Activation for Low-Temperature Wafer Direct Bonding M. Reiche, M. Wiegand, V. Dragoi	292
--	-----

PHOTONIC APPLICATIONS

Application of Wafer-Bonding to Coherent Light Sources in the Infrared and Visible Spectra S.J. Ben Yoo (Invited)	302
---	-----

Contact Angle Measurement of Wafer Surfaces for Integrating Laser Diode and Optical Isolator by Wafer Bonding H. Yokoi, T. Mizumoto, M. Shimizu, T. Waniishi, N. Futakuchi, N. Kaida, Y. Nakano	311
--	-----

APPLICATION TO MICRO-ELECTRO-MECHANICAL SYSTEMS (MEMS)

Selective Fusion Bonding by Surface Roughness Control C. Gui, R.E. Oosterbroek, J.W. Berenschot, S. Schlautmann, R.S.J. Lammerink, A. van den Berg, M.C. Elwenspoek	318
An Electro-Mechanical Analysis of the Anodic Bond Process for Microelectromechanical Systems S.J. Cunningham, D.R. DeReus, J.W. Borninski	326
Characterization of Wafer Bond Toughness P.E.W. Labossiere, M.L. Dunn, S.J. Cunningham	338
State of the Art Deep Silicon Anisotropic Etching on SOI Bonded Substrates for Dielectric Isolation and MEMS Applications C. Gormley, K. Yallup, W.A. Nevin, J. Bhardwaj, H. Ashraf, P. Huggett, S. Blackstone	350
Pressure Sensor for Harsh Environments Realised by Triple Stack Fusion Bonding M.M. Visser, J.A. Plaza, D.T. Wang, S.T. Moe, K. Schjølberg-Henriksen, A.B. Hanneborg	362
Application of High and Low Wafer Bonding Processes for Bulk Micromachined Components M. Wiemer, K. Hiller, R. Hahn, C. Kaufmann, T. Gessner	368
The Use of Selective Anodic Bonding to Create Near-Zero Dead Volume Membranes T.T. Veenstra, J.W. Berenschot, J.G.E. Gardeniers, R.G.P. Sanders, M.C. Elwenspoek, A. van den Berg	381

NOVEL APPLICATIONS

VCSEL and High-Performance Photonics Enabled by Wafer Bonding P. Abraham, K.A. Black, B. Liu, J. Piprek, Y.J. Chiu, A. Karim, A. Shakouri, S.K. Mathis, E.L. Hu, J.E. Bowers (Invited)	386
Form C Opto-Solid State Relay on Bonded Wafer with 1600V Isolation P. Sinclair, D. Whitney, W. Taggart, K. Yallup, S. Blackstone	402
Micromachined, Electrostatically-Actuated Optical Attenuators/Switches Fabricated by Fusion Bonding of Single-Crystal, Ultra-Thin Silicon Wafers R.A. Brown, V.A. Aksyuk, K.R. Farmer	407
3-D Self Assembly of Opto-Mechanical Structures Using Bonded Silicon-on-Insulator R.R.A. Syms, S. Blackstone	415
Depleted Semi-Insulating Silicon/Silicon Material Formed by Wafer Bonding Mikael Johansson, Stefan Bengtsson	420

Low Temperature Anodic Bonding of a Sub- μ Fabry-Perot Cavity
Åse Richard, Kjell Sundin, Ylva Bäckland429

Complementary Bipolar Fabricated by the Bonding of Patterned Buried Layers
P. Irissou, V. Pilloud, K.Yallup, A. Brown, G. Gaston, S. Blackstone438

HIGH-VOLTAGE, HIGH-POWER APPLICATIONS

Application of Bonded SOI to Dielectric Isolation for 250V Devices
Atsuo Hirabayashi, Hitoshi Sumida, Hiroshi Shimabukuro (Invited)443

A Comparison of Large Area, High Voltage Power Electronic Devices
Fabricated With and Without Wafer Bonding
Cynthia A. Colinge, Getachew Ayele, Rogerio Rodrigues, Dante Piccone,
Mukesh Patel453

High Breakdown Voltage CMOS Transistor with Intrinsic SOI Substrate
Hitoshi Yamaguchi, Shigeyuki Akita, Hiroaki Himi, Kazunori Kawamoto459

HVIC Process on Bonded Wafers with Internal Gettering
N. Polce, M. Calley, S. Jones, S. Blackstone, P. Martin470

AUTHOR INDEX473

SUBJECT INDEX477